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Yuanlin Xie, Wenqin Cheng, Yi Huang, Zhenghao Chen, Zhidong Lu, Guozhen Yang, Shijie Gu and Junming Zhou, Study on optical properties of planar modulation structures of AlGaAs/GaAs superlattices and quantum wells 228 (1990) 403
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J.S. Weiner, G. Danan, A. Pinczuk, J.P. Valladares, L.N. Pfeiffer and K.W. West, Optical spectroscopy of one-dimensional confinement in multiple quantum wires 228 (1990) 412
K. Kash, J.M. Worlock, D.D. Mahoney, A.S. Gozdz, B.P. van der Gaag, J.P. Harbison, P.S.D. Lin and L.T. Florez, Optical properties of quantum wires produced by strain patterning of GaAs–AlGaAs quantum wells 228 (1990) 415
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B. Lambert, B. Deveaud, A. Chomette, F. Clerot, A. Regreny and B. Sermage, Temperature dependence of electronic vertical transport in short period GaAs–AlGaAs superlattices 228 (1990) 446

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R. Heinrich, R. Zachai, M. Besson, T. Egeler, G. Abstreiter, W. Schlapp and G. Weimann, Negative infrared photoconductivity in narrow GaAs/AlGaAs multiple quantum well structures 228 (1990) 465

K.J. Duff and K.C. Hass, Multi-band envelope function calculations for sawtooth superlattices 228 (1990) 479

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N.F. Johnson and H. Ehrenreich, Infrared optical properties of III–V and II–VI superlattices 228 (1990) 197

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S.Y. Ren, J. Shen, Run-Di Hong, S. Klemm, M.-H. Tsai and J.D. Dow, Deep levels and shallow–deep transi-

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S. Ben Amor, K.P. Martin, J.J.L. Rascol, R.J. Higgins, R.C. Potter, A.A. Lakhani and H. Hier, Magneto-electric states in wide-well double barrier tunneling structures 228 (1990) 378
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H. Wang, J.T. Remillard, M.D. Webb, D.G. Steel, J. Pamulapati, J.E. Oh and P.K. Bhattacharya, High resolution laser spectroscopy of relaxation and the excitation lineshape of excitons in GaAs quantum well structures 228 (1990) 69

F. Agulló-Rueda, E.E. Mendez, J.A. Brum and J.M. Hong, Coherence and localization in superlattices under electric fields 228 (1990) 80

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C.S. Baxter, R.F. Broom and W.M. Stobbs, The characterisation of the ordering of MOVPE grown III–V alloys using transmission electron microscopy 228 (1990) 102

A. Krol, C.J. Sher, D.R. Storch, S.C. Woronick, Y.H. Kao, L.L. Chang and H. Munekata, Soft X-ray investigation of the effect of growth conditions on InAs/GaAs heterostructures 228 (1990) 108

M. Olszakier, E. Ehrenfreund, E. Cohen, J. Bajaj and G.J. Sullivan, Intersubband absorption by photoinduced excitons in undoped multi-quantum-wells 228 (1990) 123

M.C. Tatham, J.F. Ryan and C.T. Foxon, Time-resolved Raman scattering measurement of electron–optical phonon intersubband relaxation in GaAs quantum wells 228 (1990) 127

M. Nakayama, M. Ishida and N. Sano, Interface-phonon polaritons in GaAs/AlAs heterostructures 228 (1990) 131

M. Recio, G. Armelles, A. Ruiz, A. Mazuelas and F. Briones, Strain distribution and structural characterization of short period GaAs–GaP strained superlattices by Raman and X-ray scattering 228 (1990) 139

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E. Lach, G. Lehr, A. Forchel, K. Ploog and G. Weimann, Investigation of the 2D–3D transition of the band gap renormalization in GaAs 228 (1990) 168
H. Tsuchiya, Y. Shakuda and H. Katahama, Intersubband absorption changes in GaAs/AlGaAs MQW induced by external light 228 (1990) 172
F. Calle, J.M. Calleja, C. Tejedor, F. Briones, J.L. de Miguel and K. Ploog, Resonant Raman scattering in GaAs–AlAs coupled double wells 228 (1990) 176
I. Brener, E. Cohen, A. Ron and L.N. Pfeiffer, Resonant Raman scattering by acceptors and LO phonons in GaAs/AlGaAs multiple quantum wells 228 (1990) 180
D.D. Smith, M. Dutta, X.C. Liu, A.F. Terzis, A. Petrou, M.W. Cole and P.G. Newman, GaAs–AlAs quantum well magneto-exciton spectrum – theory and experiment 228 (1990) 184
A. Salvador, J. Reed, N.S. Kumar. M.S. Ünlü and H. Morkoç, Electroabsorption studies on GaAs asymmetric coupled quantum wells 228 (1990) 188
M. Sato and Y. Horikoshi, Photoluminescence from GaAs/AlGaAs quantum wells with InAs monomolecular planes grown by flow-rate modulation epitaxy 228 (1990) 192
C. López, F. Meseguer, J. Sánchez-Dehesa and K. Ploog, Magnetoluminescence studies of modulation n-doped GaAs–AlGaAs multiple quantum wells 228 (1990) 202
H. Fujimoto, C. Hamaguchi, T. Nakazawa, K. Imanishi, K. Taniguchi and S. Sasa, Direct and indirect transitions in $(GaAs)_m/(AlAs)_5$ superlattices 228 (1990) 206
B. Lambert, B. Sermage, B. Deveaud, F. Clerot, A. Chomette and A. Regreny, Radiative and non-radiative recombination in GaAs–AlGaAs superlattices 228 (1990) 210
G. Scamarcio, A. Cingolani, R. Cingolani and K. Ploog, Optical and vibrational properties of $Al_xGa_{1-x}As$/AlAs multiple quantum wells near the direct indirect cross-over 228 (1990) 213
R. Cingolani, M. Holtz, R. Muralidharan, K. Ploog, K. Reimann and K. Syassen, Type I–type II transition in ultra short period GaAs/AlAs superlattices revealed by luminescence under high-excitation intensity and high pressure 228 (1990) 217
E.F. Schubert, Optical properties of δ-doped doping superlattices 228 (1990) 240
G. Tempel, F. Müller, N. Schwarz, F. Koch, G. Weimann, H.P. Zeindl and I. Eisele, Infrared excitation of the subbands of a δ-layer in GaAs and Si 228 (1990) 247
A.C. Maciel, M.C. Tatham, J.F. Ryan, J.M. Worlock, R.E. Nahory, J.P. Harbison and L.T. Florez, Raman scattering from electronic excitations in periodically δ-doped GaAs 228 (1990) 251
M. Santos, T. Sajoto, A.-M. Lanzillotto, A. Zrenner and M. Shayegan, Migration of Si in δ-doped GaAs and $Al_xGa_{1-x}As$: effect of substrate temperature 228 (1990) 255
C.M. Sotomayor Torres, M. Watt, H.E.G. Arnot, R. Glew, R. Cusco Cornet, T.M. Kerr, S. Thoms and S.P. Beaumont, Optical spectroscopy of GaAs-based nanostructures 228 (1990) 275
Y. Tokura, K. Tsubaki and N. Susa, Electronic states in an AlGaAs–GaAs modulation-doped hetero-interface with a 10 nm-order periodic structure 228 (1990) 280
J. Spector, H.L. Stormer, K.W. Baldwin, L.N. Pfeiffer and K.W. West, Ballistic electron transport beyond 100 μm in 2D electron systems 228 (1990) 283
K. Ishibashi, S.K. Noh, Y. Aoyagi, S. Namba, M. Mizuno, Y. Ochiai, M. Kawabe and K. Gamo, Low temperature magnetoresistance in a narrow wire of GaAs/AlGaAs 228 (1990) 286
R.P. Taylor, P.C. Main, L. Eaves, S.P. Beaumont, I. McIntyre, S. Thoms and C.D.W. Wilkinson, Electronic properties of laterally confined n-GaAs/(AlGa)As heterostructures 228 (1990) 296
F. Laruelle, Y.P. Hu, R. Simes, W. Robinson, J. Merz and P.M. Petroff, Optical study of GaAs/GaAlAs quantum structures processed by high energy focused ion beam implantation 228 (1990) 306
G. Duggan, K.J. Moore, K. Woodbridge and C. Roberts, (InGa)As–GaAs strained layer quantum wells – excitonic properties and electronic structure 228 (1990) 310
E.S. Koteles, D.A. Owens, D.C. Bertolet, Jung-Kuei Hsu and Kei May Lau, Reversal of light- and heavy-hole valence bands in strained GaAsP/AlGaAs quantum wells 228 (1990) 314
W. Chen, M. Fritze, Q. Fu, A.V. Nurmikko, C. Colvard, D. Ackley and H. Lee, Magnetic field induced

quenching of excitons in modulation doped InGaAs quantum wells 228 (1990) 318

A. Ksendzov, H. Shen, F.H. Pollak and D.P. Bour, Photoreflectance study of $In_xGa_{1-x}As/GaAs$ single quantum wells 228 (1990) 326

E.D. Jones, R.M. Biefeld, J.F. Klem, S.K. Lyo and G.C. Osbourn, Valence-band characterization of InGaAs/GaAs and GaAs/GaAsP strained-layer structures 228 (1990) 330

H. Nickel, R. Lösch, W. Schlapp, H. Leier and A. Forchel, $In_xGa_{1-x}As/GaAs$ pseudomorphic quantum wells – growth and thermal stability 228 (1990) 340

D. Morris, C. Lacelle, A.P. Roth, P. Maigne and J.L. Brebner, Optical and structural characterization of InGaAs/GaAs superlattices with increasing number of periods 228 (1990) 347

X.M. Fang, X.C. Shen, H.Q. Hou, W. Feng, J.M. Zhou and F. Koch, Photocurrent spectroscopy of strained-layer InGaAs–GaAs multiple quantum wells 228 (1990) 351

P. Basmaji, A.M. Ceschin, M. Siu Li, O. Hipólito, A.A. Bernussi, F. Iikawa and P. Motisuke, MBE growth and characterization of δ-doping in GaAs and GaAs/Si 228 (1990) 356

H. Schneider, H.T. Grahn and K. von Klitzing, Tunneling resonances and miniband conduction in superlattices 228 (1990) 362

S. Muto, A. Tackeuchi, T. Inata, E. Miyauchi and T. Fujii, Picosecond characterization of InGaAs/InAlAs resonant tunneling barriers grown by MBE 228 (1990) 370

S. Ben Amor, K.P. Martin, J.J.L. Rascol, R.J. Higgins, R.C. Potter, A.A. Lakhani and H. Hier, Magneto-electric states in wide-well double barrier tunneling structures 228 (1990) 378

H.W. Liu, R. Ferreira, G. Bastard, C. Delalande, J.F. Palmier and B. Etienne, Optical study of assisted tunneling in biased double quantum well structures 228 (1990) 383

C.G. Smith, M. Pepper, H. Ahmed, J.E.F. Frost, D.G. Hasko, R. Newbury, D.C. Peacock, D.A. Ritchie and G.A.C. Jones, One dimensional electron tunneling and related phenomena 228 (1990) 387

T.B. Norris, G.A. Mourou, X.J. Song, L.F. Eastman, N. Vodjdani, B. Vinter and C. Weisbuch, Time-resolved photoluminescence spectroscopy of GaAs quantum well tunneling structures 228 (1990) 393

G. Berthold, J. Smoliner, G. Strasser, E. Gornik and G. Weimann, Subbands and photoconductivity in two barrier-separated 2D electron gas systems 228 (1990) 399

Yuanlin Xie, Wenqin Cheng, Yi Huang, Zhenghao Chen, Zhidong Lu, Guozhen Yang, Shijie Gu and Junming Zhou, Study on optical properties of planar modulation structures of AlGaAs/GaAs superlattices and quantum wells 228 (1990) 403

M. Tanaka, J. Motohisa and H. Sakaki, Formation of in-plane superlattice and quantum wire states in grid inserted heterostructures with period of 80–160 Å: anisotropy of electronic states 228 (1990) 408

J.S. Weiner, G. Danan, A. Pinczuk, J.P. Valladares, L.N. Pfeiffer and K.W. West, Optical spectroscopy of one-dimensional confinement in multiple quantum wires 228 (1990) 412

K. Kash, J.M. Worlock, D.D. Mahoney, A.S. Gozdz, B.P. van der Gaag, J.P. Harbison, P.S.D. Lin and L.T. Florez, Optical properties of quantum wires produced by strain patterning of GaAs–AlGaAs quantum wells 228 (1990) 415

I. Mehdi, R.K. Mains, G.I. Haddad and U.K. Reddy, Properties and device applications of deep quantum well resonant tunneling structures 228 (1990) 426

S.S. Lu, K.R. Lee, K.H. Lee, M.I. Nathan, M. Heiblum and S.L. Wright, Excess current in $n^+GaAs–Al_xGa_{1-x}As–nGaAs$ heterojunctions 228 (1990) 430

M. Henini, M.L. Leadbeater, E.S. Alves, L. Eaves, O.H. Hughes, G. Hill and M.A. Pate, The effect of conduction band anisotropy on hybrid magneto-electric states in resonant tunneling devices 228 (1990) 433

H. Le Person, J.F. Palmier, C. Minot, J.C. Esnault and F. Mollot, Time of flight of electrons and holes at 77 and 300 K in GaAs/AlAs superlattices 228 (1990) 441

B. Lambert, B. Deveaud, A. Chomette, F. Clerot, A. Regreny and B. Sermage, Temperature dependence of electronic vertical transport in short period GaAs–AlGaAs superlattices 228 (1990) 446

K. Zekentes, S. Ravanomanjato, R. Piotrzkowski, E. Litwin-Staszewska, J.L. Robert, J.P. Andre and P.M. Frijlink, Weak localization of 2D electron

gas in GaAs–$Ga_{1-x}Al_xAs$ heterostructures under hydrostatic pressure 228 (1990) 449
Qiu-yi Ye, A. Zrenner, F. Koch, H. Sigg, D. Heitmann and K. Ploog, Mobility enhancement by regular positioning of donor impurities 228 (1990) 453
K. Ensslin, D. Heitmann and K. Ploog, Influence of the exchange interaction on the population process of the upper subband 228 (1990) 456
J.A. Levenson, G. Dolique, J.L. Oudar and I. Abram, Dynamics of the intersubband relaxation of thermalized carriers in GaAs/GaAlAs multiple quantum wells 228 (1990) 461
R. Heinrich, R. Zachai, M. Besson, T. Egeler, G. Abstreiter, W. Schlapp and G. Weimann, Negative infrared photoconductivity in narrow GaAs/AlGaAs multiple quantum well structures 228 (1990) 465
K.J. Duff and K.C. Hass, Multi-band envelope function calculations for sawtooth superlattices 228 (1990) 479
A. Wixforth, M. Sundaram, D. Donnelly, J.H. English and A.C. Gossard, Graded potential wells with quasi-uniform charge distribution 228 (1990) 489
H. Ohno, K. Matsuzaki, H. Tomozawa, J.K. Luo and H. Hasegawa, Carrier concentration in selectively doped n-AlGaAs/GaAs single heterojunctions 228 (1990) 497
P.S. Kop'ev, SCH lasers using short period superlattices 228 (1990) 514
R.A. Puechner, Jun Ma, R. Mezenner, W.-P. Liu, A.M. Kriman, G.N. Maracas, G. Bernstein, D.K. Ferry, P. Chu, H.H. Wieder and P.G. Newman, Magnetoconductance in lateral surface superlattices 228 (1990) 520
C.T. Liu, K. Nakamura, D.C. Tsui, K. Ismail, D.A. Antoniadis and H.I. Smith, Far-infrared transmission measurements on grid-gate GaAs/AlGaAs lateral-surface-superlattice structures 228 (1990) 527
P.M. Koenraad, A.P.J. Voncken, J. Singleton, F.A.P. Blom, C.J.G.M. Langerak, M.R. Leys, J.A.A.J. Perenboom, S.J.R.M. Spermon, W.C. van Vleuten and J.H. Wolter, Characterization of silicon δ-doped GaAs grown by MBE at various temperatures 228 (1990) 538

Gallium phosphide

M. Recio, G. Armelles, A. Ruiz, A. Mazuelas and F. Briones, Strain distribution and structural characterization of short period GaAs–GaP strained superlattices by Raman and X-ray scattering 228 (1990) 139
E.S. Koteles, D.A. Owens, D.C. Bertolet, Jung-Kuei Hsu and Kei May Lau, Reversal of light- and heavy-hole valence bands in strained GaAsP/AlGaAs quantum wells 228 (1990) 314

Germanium

T.A. Gant, D.J. Lockwood, J.-M. Baribeau and A.H. MacDonald, Raman scattering studies of phonons in quasiperiodic superlattices based on generalizations of the Fibonacci sequence 228 (1990) 135
R. Zachai, K. Eberl, G. Abstreiter, E. Kasper and H. Kibbel, Photoluminescence in short period Si/Ge strained layer superlattices grown on Si and Ge substrates 228 (1990) 267
Xun Wang, K.M. Chen, G.L. Jin, C. Sheng, G.L. Zhou, W.D. Jiang, X.J. Zhang and M.R. Yu, RHEED intensity oscillations of MBE grown Ge/Si ultra-thin multi-layered structures 228 (1990) 334

Heterostructures

T. Sands, J.P. Harbison, N. Tabatabaie, W.K. Chan, H.L. Gilchrist, T.L. Cheeks, L.T. Florez and V.G. Keramidas, Epitaxial metal(NiAl)–semiconductor(III–V) heterostructures by MBE 228 (1990) 1
J.E. Oh, P.K. Bhattacharya, J. Singh, W. Dos Passos, R. Clarke, N. Mestres, R. Merlin, K.H. Chang and R. Gibala, Epitaxial growth and characterization of GaAs/Al/GaAs heterostructures 228 (1990) 16
S.M. Durbin, M. Kobayashi, Q. Fu, N. Pelekanos, R.L. Gunshor and A.V. Nurmikko, ZnTe/MnTe: a new metastable wide gap II–VI heterostructure 228 (1990) 33
M. Potemski, J.C. Maan, T.P. Smith and L.L. Chang, Strong blue shift of the luminescence of indirect AlAs/GaAlAs quantum wells with excitation intensity 228 (1990) 57
J. Richter, H. Sigg, K. von Klitzing and K. Ploog, Cyclotron resonance of two-dimensional electron systems under the influence of ionized impurity-scattering 228 (1990) 159
J. Spector, H.L. Stormer, K.W. Baldwin, L.N. Pfeiffer and K.W. West, Ballistic

electron transport beyond 100 μm in 2D electron systems 228 (1990) 283
R.P. Taylor, P.C. Main, L. Eaves, S.P. Beaumont, I. McIntyre, S. Thoms and C.D.W. Wilkinson, Electronic properties of laterally confined n-GaAs/(AlGa)As heterostructures 228 (1990) 296
S.S. Lu, K.R. Lee, K.H. Lee, M.I. Nathan, M. Heiblum and S.L. Wright, Excess current in n^+GaAs–$Al_xGa_{1-x}As$–nGaAs heterojunctions 228 (1990) 430
K. Zekentes, S. Ravanomanjato, R. Piotrzkowski, E. Litwin-Staszewska, J.L. Robert, J.P. Andre and P.M. Frijlink, Weak localization of 2D electron gas in GaAs–$Ga_{1-x}Al_xAs$ heterostructures under hydrostatic pressure 228 (1990) 449
J.A. Levenson, G. Dolique, J.L. Oudar and I. Abram, Dynamics of the intersubband relaxation of thermalized carriers in GaAs/GaAlAs multiple quantum wells 228 (1990) 461
J.-H. Reemtsma, H. Meschede, W. Brockerhoff, K. Heime, W. Schlapp and G. Weimann, Properties of p-type heterostructure field effect transistors at cryogenic temperatures 228 (1990) 472
S.K. Lyo, Phonon-drag thermoelectric power in high magnetic fields in heterojunctions 228 (1990) 493
H. Ohno, K. Matsuzaki, H. Tomozawa, J.K. Luo and H. Hasegawa, Carrier concentration in selectively doped n-AlGaAs/GaAs single heterojunctions 228 (1990) 497
S.K. Greene, J. Singleton, T.D. Golding, M. Pepper, C.J.G.M. Langerak and J.H. Dinan, Fundamental properties of high mobility InSb–CdTe heterojunctions 228 (1990) 542

Indium antimonide

M. Helm, P. England, E. Colas, F. DeRosa and S.J. Allen, Jr., Intersubband emission from quantum wells and superlattices 228 (1990) 120
R.J. Warburton, G.M. Sundaram, R.J. Nicholas, S.K. Haywood, G.J. Rees, N.J. Mason and P.J. Walker, Strain reconstruction of the valence band in $Ga_{1-x}In_xSb$/GaSb quantum wells 228 (1990) 270
T.J. Gregory, J.E. Nicholls, J.J. Davies, C.P. Hilton, W.E. Hagston, B. Lunn and D.E. Ashenford, Band offset determination in $CdTe/Cd_{1-x}Mn_xTe$ MQWs grown on InSb substrates 228 (1990) 359
S.K. Greene, J. Singleton, T.D. Golding, M. Pepper, C.J.G.M. Langerak and J.H. Dinan, Fundamental properties of high mobility InSb–CdTe heterojunctions 228 (1990) 542

Indium arsenide

A. Krol, C.J. Sher, D.R. Storch, S.C. Woronick, Y.H. Kao, L.L. Chang and H. Munekata, Soft X-ray investigation of the effect of growth conditions on InAs/GaAs heterostructures 228 (1990) 108
R. Ranganathan, B.S. Yoo, Y.J. Wang, B.D. McCombe, K.Y. Lim, F. Kuchar, K. Elcess and C. Fonstad, Cyclotron resonance in ⟨111⟩-oriented InGaAs/AlGaAs strained layer superlattices 228 (1990) 156
M. Sato and Y. Horikoshi, Photoluminescence from GaAs/AlGaAs quantum wells with InAs monomolecular planes grown by flow-rate modulation epitaxy 228 (1990) 192
G. Duggan, K.J. Moore, K. Woodbridge and C. Roberts, (InGa)As–GaAs strained layer quantum wells – excitonic properties and electronic structure 228 (1990) 310
W. Chen, M. Fritze, Q. Fu, A.V. Nurmikko, C. Colvard, D. Ackley and H. Lee, Magnetic field induced quenching of excitons in modulation doped InGaAs quantum wells 228 (1990) 318
A. Ksendzov, H. Shen, F.H. Pollak and D.P. Bour, Photoreflectance study of $In_xGa_{1-x}As$/GaAs single quantum wells 228 (1990) 326
E.D. Jones, R.M. Biefeld, J.F. Klem, S.K. Lyo and G.C. Osbourn, Valence-band characterization of InGaAs/GaAs and GaAs/GaAsP strained-layer structures 228 (1990) 330
H. Nickel, R. Lösch, W. Schlapp, H. Leier and A. Forchel, $In_xGa_{1-x}As$/GaAs pseudomorphic quantum wells – growth and thermal stability 228 (1990) 340
D. Morris, C. Lacelle, A.P. Roth, P. Maigne and J.L. Brebner, Optical and structural characterization of InGaAs/GaAs superlattices with increasing number of periods 228 (1990) 347
X.M. Fang, X.C. Shen, H.Q. Hou, W. Feng, J.M. Zhou and F. Koch, Photocurrent spectroscopy of strained-layer InGaAs–GaAs multiple quantum wells 228 (1990) 351

S. Muto, A. Tackeuchi, T. Inata, E. Miyauchi and T. Fujii, Picosecond characterization of InGaAs/InAlAs resonant tunneling barriers grown by MBE 228 (1990) 370
S. Ben Amor, K.P. Martin, J.J.L. Rascol, R.J. Higgins, R.C. Potter, A.A. Lakhani and H. Hier, Magneto-electric states in wide-well double barrier tunneling structures 228 (1990) 378
R.A. Puechner, Jun Ma, R. Mezenner, W.-P. Liu, A.M. Kriman, G.N. Maracas, G. Bernstein, D.K. Ferry, P. Chu, H.H. Wieder and P.G. Newman, Magnetoconductance in lateral surface superlattices 228 (1990) 520

Indium phosphide

C.S. Baxter, R.F. Broom and W.M. Stobbs, The characterisation of the ordering of MOVPE grown III–V alloys using transmission electron microscopy 228 (1990) 102
I. Mehdi, R.K. Mains, G.I. Haddad and U.K. Reddy, Properties and device applications of deep quantum well resonant tunneling structures 228 (1990) 426

Infrared spectroscopy

D. Gammon, B.V. Shanabrook and W. Tseng, A Raman scattering and far-infrared magneto-absorption study of donors in a quasi-two-dimensional electron gas 228 (1990) 147
N.F. Johnson and H. Ehrenreich, Infrared optical properties of III–V and II–VI superlattices 228 (1990) 197
G. Tempel, F. Müller, N. Schwarz, F. Koch, G. Weimann, H.P. Zeindl and I. Eisele, Infrared excitation of the subbands of a δ-layer in GaAs and Si 228 (1990) 247
S.A. Lyon, Long wavelength quantum well detectors: can they compete? 228 (1990) 508
J. Alsmeier, E. Batke and J.P. Kotthaus, The transition to quasi one- or zero-dimensionality in laterally periodic MOS devices on silicon 228 (1990) 524
C.T. Liu, K. Nakamura, D.C. Tsui, K. Ismail, D.A. Antoniadis and H.I. Smith, Far-infrared transmission measurements on grid-gate GaAs/AlGaAs lateral-surface-superlattice structures 228 (1990) 527
P.M. Koenraad, A.P.J. Voncken, J. Singleton, F.A.P. Blom, C.J.G.M. Langerak, M.R. Leys, J.A.A.J. Perenboom, S.J.R.M. Spermon, W.C. van Vleuten and J.H. Wolter, Characterization of silicon δ-doped GaAs grown by MBE at various temperatures 228 (1990) 538

Ion implantation

F. Laruelle, Y.P. Hu, R. Simes, W. Robinson, J. Merz and P.M. Petroff, Optical study of GaAs/GaAlAs quantum structures processed by high energy focused ion beam implantation 228 (1990) 306

Lead telluride

H. Clemens, H. Krenn, P.C. Weilguni, U. Stromberger, G. Bauer and H. Pascher, Growth and characterization of dilute magnetic PbTe/$Pb_{1-x}Mn_xTe$ superlattices 228 (1990) 236

Luminescence

T. Fukui, H. Saito, Y. Tokura, K. Tsubaki and N. Susa, $(AlAs)_{1/2}(GaAs)_{1/2}$ fractional-layer superlattices grown on (001) vicinal GaAs substrates by MOCVD 228 (1990) 20
M.P. Halsall, J.E. Nicholls, J.J. Davies, P.J. Wright and B. Cockayne, Photoluminescence studies of CdS/CdSe wurtzite superlattices; evidence for large piezoelectric effects 228 (1990) 41
M. Potemski, J.C. Maan, T.P. Smith and L.L. Chang, Strong blue shift of the luminescence of indirect AlAs/GaAlAs quantum wells with excitation intensity 228 (1990) 57
H.T. Grahn, H. Schneider and K. von Klitzing, Spatial distribution of high-field domains in GaAs–AlAs superlattices 228 (1990) 84
M. Sato and Y. Horikoshi, Photoluminescence from GaAs/AlGaAs quantum wells with InAs monomolecular planes grown by flow-rate modulation epitaxy 228 (1990) 192
C. López, F. Meseguer, J. Sánchez-Dehesa and K. Ploog, Magnetoluminescence studies of modulation n-doped GaAs–AlGaAs multiple quantum wells 228 (1990) 202

H. Fujimoto, C. Hamaguchi, T. Nakazawa, K. Imanishi, K. Taniguchi and S. Sasa, Direct and indirect transitions in $(GaAs)_m/(AlAs)_5$ superlattices 228 (1990) 206

B. Lambert, B. Sermage, B. Deveaud, F. Clerot, A. Chomette and A. Regreny, Radiative and non-radiative recombination in GaAs–AlGaAs superlattices 228 (1990) 210

G. Scamarcio, A. Cingolani, R. Cingolani and K. Ploog, Optical and vibrational properties of $Al_xGa_{1-x}As/AlAs$ multiple quantum wells near the direct indirect cross-over 228 (1990) 213

R. Cingolani, M. Holtz, R. Muralidharan, K. Ploog, K. Reimann and K. Syassen, Type I–type II transition in ultra short period GaAs/AlAs superlattices revealed by luminescence under high-excitation intensity and high pressure 228 (1990) 217

N. Samarth, H. Luo, J.K. Furdyna, S.B. Qadri, Y.R. Lee, R.G. Alonso, E.K. Suh, A.K. Ramdas and N. Otsuka, Molecular beam epitaxy of cubic $Zn_{1-x}Cd_xSe$ and $Cd_{1-x}Mn_xSe$ and related superlattices 228 (1990) 226

M.R. Freeman, D.D. Awschalom, J.M. Hong and L.L. Chang, Ultrafast polarization spectroscopy of diluted magnetic semiconductor superlattices 228 (1990) 233

E.F. Schubert, Optical properties of δ-doped doping superlattices 228 (1990) 240

A.C. Maciel, M.C. Tatham, J.F. Ryan, J.M. Worlock, R.E. Nahory, J.P. Harbison and L.T. Florez, Raman scattering from electronic excitations in periodically δ-doped GaAs 228 (1990) 251

R. Zachai, K. Eberl, G. Abstreiter, E. Kasper and H. Kibbel, Photoluminescence in short period Si/Ge strained layer superlattices grown on Si and Ge substrates 228 (1990) 267

F. Laruelle, Y.P. Hu, R. Simes, W. Robinson, J. Merz and P.M. Petroff, Optical study of GaAs/GaAlAs quantum structures processed by high energy focused ion beam implantation 228 (1990) 306

G. Duggan, K.J. Moore, K. Woodbridge and C. Roberts, (InGa)As–GaAs strained layer quantum wells – excitonic properties and electronic structure 228 (1990) 310

E.S. Koteles, D.A. Owens, D.C. Bertolet, Jung-Kuei Hsu and Kei May Lau, Reversal of light- and heavy-hole valence bands in strained GaAsP/AlGaAs quantum wells 228 (1990) 314

W. Chen, M. Fritze, Q. Fu, A.V. Nurmikko, C. Colvard, D. Ackley and H. Lee, Magnetic field induced quenching of excitons in modulation doped InGaAs quantum wells 228 (1990) 318

B. Rockwell, H.R. Chandrasekhar, M. Chandrasekhar, F.H. Pollak, H. Shen, L.L. Chang, W.I. Wang and L. Esaki, Spectroscopic studies of strained-layer GaSb–AlSb superlattices 228 (1990) 322

E.D. Jones, R.M. Biefeld, J.F. Klem, S.K. Lyo and G.C. Osbourn, Valence-band characterization of InGaAs/GaAs and GaAs/GaAsP strained-layer structures 228 (1990) 330

H. Nickel, R. Lösch, W. Schlapp, H. Leier and A. Forchel, $In_xGa_{1-x}As/GaAs$ pseudomorphic quantum wells – growth and thermal stability 228 (1990) 340

D.L. Mathine, S.M. Durbin, R.L. Gunshor, M. Kobayashi, D.R. Menke, J.M. Gonsalves, N. Otsuka, Q. Fu, M. Hagerott and A.V. Nurmikko, Molecular beam epitaxy of pseudomorphic ZnTe/AlSb/GaSb 228 (1990) 344

D. Morris, C. Lacelle, A.P. Roth, P. Maigne and J.L. Brebner, Optical and structural characterization of InGaAs/GaAs superlattices with increasing number of periods 228 (1990) 347

T.J. Gregory, J.E. Nicholls, J.J. Davies, C.P. Hilton, W.E. Hagston, B. Lunn and D.E. Ashenford, Band offset determination in $CdTe/Cd_{1-x}Mn_xTe$ MQWs grown on InSb substrates 228 (1990) 359

H. Schneider, H.T. Grahn and K. von Klitzing, Tunneling resonances and miniband conduction in superlattices 228 (1990) 362

D.G. Hayes, M.S. Skolnick, P.E. Simmonds, L. Eaves, D.P. Halliday, M.L. Leadbeater, M. Henini, O.H. Hughes, G. Hill and M.A. Pate, Optical investigation of charge accumulation and bistability in an asymmetric double barrier resonant tunneling heterostructure 228 (1990) 373

H.W. Liu, R. Ferreira, G. Bastard, C. Delalande, J.F. Palmier and B. Etienne, Optical study of assisted tunneling in biased double quantum well structures 228 (1990) 383

T.B. Norris, G.A. Mourou, X.J. Song, L.F. Eastman, N. Vodjdani, B. Vinter and C. Weisbuch, Time-resolved photoluminescence spectroscopy of GaAs quantum well tunneling structures 228 (1990) 393

Yuanlin Xie, Wenqin Cheng, Yi Huang, Zhenghao Chen, Zhidong Lu, Guoz-

hen Yang, Shijie Gu and Junming Zhou, Study on optical properties of planar modulation structures of AlGaAs/GaAs superlattices and quantum wells 228 (1990) 403
M. Tanaka, J. Motohisa and H. Sakaki, Formation of in-plane superlattice and quantum wire states in grid inserted heterostructures with period of 80–160 Å: anisotropy of electronic states 228 (1990) 408
J.S. Weiner, G. Danan, A. Pinczuk, J.P. Valladares, L.N. Pfeiffer and K.W. West, Optical spectroscopy of one-dimensional confinement in multiple quantum wires 228 (1990) 412
K. Kash, J.M. Worlock, D.D. Mahoney, A.S. Gozdz, B.P. van der Gaag, J.P. Harbison, P.S.D. Lin and L.T. Florez, Optical properties of quantum wires produced by strain patterning of GaAs–AlGaAs quantum wells 228 (1990) 415
B. Lambert, B. Deveaud, A. Chomette, F. Clerot, A. Regreny and B. Sermage, Temperature dependence of electronic vertical transport in short period GaAs–AlGaAs superlattices 228 (1990) 446
T. Fukuzawa, S.S. Kano, T.K. Gustafson and T. Ogawa, Possibility of coherent light emission from Bose condensed states of SEHPs 228 (1990) 482
P.S. Kop'ev, SCH lasers using short period superlattices 228 (1990) 514

Magnetic measurements

S.J. Allen, Jr., N. Tabatabaie, C.J. Palmstrøm, S. Mounier, G.W. Hull, T. Sands, F. DeRosa, H.L. Gilchrist and K.C. Garrison, Magneto-transport in ultrathin ErAs epitaxial layers buried in GaAs 228 (1990) 13
N.J. Pulsford, R.J. Nicholas, P. Dawson, K.J. Moore, G. Duggan and C.T. Foxon, Γ- and X-miniband structure in GaAs–AlAs short period superlattices 228 (1990) 62
D. Gammon, B.V. Shanabrook and W. Tseng, A Raman scattering and far-infrared magneto-absorption study of donors in a quasi-two-dimensional electron gas 228 (1990) 147
D.D. Smith, M. Dutta, X.C. Liu, A.F. Terzis, A. Petrou, M.W. Cole and P.G. Newman, GaAs–AlAs quantum well magneto-exciton spectrum – theory and experiment 228 (1990) 184
C. López, F. Meseguer, J. Sánchez-Dehesa and K. Ploog, Magnetoluminescence studies of modulation n-doped GaAs–AlGaAs multiple quantum wells 228 (1990) 202
D.D. Awschalom, J.M. Hong and L.L. Chang, Magnetic observations of carrier quantization and dimensional crossover in diluted magnetic semiconductor superlattices 228 (1990) 220
S.A. Jackson, Piezomagnetism and excitons in the CdTe/Cd(Mn)Te and Cd(Mn)Te/Zn(Mn)Te quantum well systems 228 (1990) 230
M. Santos, T. Sajoto, A.-M. Lanzillotto, A. Zrenner and M. Shayegan, Migration of Si in δ-doped GaAs and $Al_xGa_{1-x}As$: effect of substrate temperature 228 (1990) 255
R.J. Warburton, G.M. Sundaram, R.J. Nicholas, S.K. Haywood, G.J. Rees, N.J. Mason and P.J. Walker, Strain reconstruction of the valence band in $Ga_{1-x}In_xSb$/GaSb quantum wells 228 (1990) 270
K. Ishibashi, S.K. Noh, Y. Aoyagi, S. Namba, M. Mizuno, Y. Ochiai, M. Kawabe and K. Gamo, Low temperature magnetoresistance in a narrow wire of GaAs/AlGaAs 228 (1990) 286
G. Platero, P.A. Schulz, L. Brey and C. Tejedor, Quantum transmission channels for magnetotunneling in semiconductor microstructures 228 (1990) 291
R.P. Taylor, P.C. Main, L. Eaves, S.P. Beaumont, I. McIntyre, S. Thoms and C.D.W. Wilkinson, Electronic properties of laterally confined n-GaAs/(AlGa)As heterostructures 228 (1990) 296
W. Chen, M. Fritze, Q. Fu, A.V. Nurmikko, C. Colvard, D. Ackley and H. Lee, Magnetic field induced quenching of excitons in modulation doped InGaAs quantum wells 228 (1990) 318
E.D. Jones, R.M. Biefeld, J.F. Klem, S.K. Lyo and G.C. Osbourn, Valence-band characterization of InGaAs/GaAs and GaAs/GaAsP strained-layer structures 228 (1990) 330
T.J. Gregory, J.E. Nicholls, J.J. Davies, C.P. Hilton, W.E. Hagston, B. Lunn and D.E. Ashenford, Band offset determination in $CdTe/Cd_{1-x}Mn_xTe$ MQWs grown on InSb substrates 228 (1990) 359
S. Ben Amor, K.P. Martin, J.J.L. Rascol, R.J. Higgins, R.C. Potter, A.A. Lakhani and H. Hier, Magneto-electric states in wide-well double barrier tunneling structures 228 (1990) 378

M. Henini, M.L. Leadbeater, E.S. Alves, L. Eaves, O.H. Hughes, G. Hill and M.A. Pate, The effect of conduction band anisotropy on hybrid magneto-electric states in resonant tunneling devices 228 (1990) 433

T.M. Fromhold, F.W. Sheard and G.A. Toombs, Effect of a transverse magnetic field on tunneling in single- and double-barrier structures 228 (1990) 437

K. Zekentes, S. Ravanomanjato, R. Piotrzkowski, E. Litwin-Staszewska, J.L. Robert, J.P. Andre and P.M. Frijlink, Weak localization of 2D electron gas in GaAs–$Ga_{1-x}Al_xAs$ heterostructures under hydrostatic pressure 228 (1990) 449

K. Ensslin, D. Heitmann and K. Ploog, Influence of the exchange interaction on the population process of the upper subband 228 (1990) 456

S.K. Lyo, Phonon-drag thermoelectric power in high magnetic fields in heterojunctions 228 (1990) 493

R.A. Puechner, Jun Ma, R. Mezenner, W.-P. Liu, A.M. Kriman, G.N. Maracas, G. Bernstein, D.K. Ferry, P. Chu, H.H. Wieder and P.G. Newman, Magnetoconductance in lateral surface superlattices 228 (1990) 520

C.T. Liu, K. Nakamura, D.C. Tsui, K. Ismail, D.A. Antoniadis and H.I. Smith, Far-infrared transmission measurements on grid-gate GaAs/AlGaAs lateral-surface-superlattice structures 228 (1990) 527

P.M. Koenraad, A.P.J. Voncken, J. Singleton, F.A.P. Blom, C.J.G.M. Langerak, M.R. Leys, J.A.A.J. Perenboom, S.J.R.M. Spermon, W.C. van Vleuten and J.H. Wolter, Characterization of silicon δ-doped GaAs grown by MBE at various temperatures 228 (1990) 538

S.K. Greene, J. Singleton, T.D. Golding, M. Pepper, C.J.G.M. Langerak and J.H. Dinan, Fundamental properties of high mobility InSb–CdTe heterojunctions 228 (1990) 542

Manganese

D.D. Awschalom, J.M. Hong and L.L. Chang, Magnetic observations of carrier quantization and dimensional crossover in diluted magnetic semiconductor superlattices 228 (1990) 220

S.A. Jackson, Piezomagnetism and excitons in the CdTe/Cd(Mn)Te and Cd(Mn)Te/Zn(Mn)Te quantum well systems 228 (1990) 230

M.R. Freeman, D.D. Awschalom, J.M. Hong and L.L. Chang, Ultrafast polarization spectroscopy of diluted magnetic semiconductor superlattices 228 (1990) 233

H. Clemens, H. Krenn, P.C. Weilguni, U. Stromberger, G. Bauer and H. Pascher, Growth and characterization of dilute magnetic PbTe/$Pb_{1-x}Mn_xTe$ superlattices 228 (1990) 236

T.J. Gregory, J.E. Nicholls, J.J. Davies, C.P. Hilton, W.E. Hagston, B. Lunn and D.E. Ashenford, Band offset determination in CdTe/$Cd_{1-x}Mn_xTe$ MQWs grown on InSb substrates 228 (1990) 359

Molecular beam epitaxy

T. Sands, J.P. Harbison, N. Tabatabaie, W.K. Chan, H.L. Gilchrist, T.L. Cheeks, L.T. Florez and V.G. Keramidas, Epitaxial metal(NiAl)–semiconductor(III–V) heterostructures by MBE 228 (1990) 1

P.M. Petroff, M. Tsuchiya and L.A. Coldren, Self-organizing epitaxial growth for the deposition of novel superlattices 228 (1990) 24

A. Krol, C.J. Sher, D.R. Storch, S.C. Woronick, Y.H. Kao, L.L. Chang and H. Munekata, Soft X-ray investigation of the effect of growth conditions on InAs/GaAs heterostructures 228 (1990) 108

N. Samarth, H. Luo, J.K. Furdyna, S.B. Qadri, Y.R. Lee, R.G. Alonso, E.K. Suh, A.K. Ramdas and N. Otsuka, Molecular beam epitaxy of cubic $Zn_{1-x}Cd_xSe$ and $Cd_{1-x}Mn_xSe$ and related superlattices 228 (1990) 226

Xun Wang, K.M. Chen, G.L. Jin, C. Sheng, G.L. Zhou, W.D. Jiang, X.J. Zhang and M.R. Yu, RHEED intensity oscillations of MBE grown Ge/Si ultra-thin multi-layered structures 228 (1990) 334

D.L. Mathine, S.M. Durbin, R.L. Gunshor, M. Kobayashi, D.R. Menke, J.M. Gonsalves, N. Otsuka, Q. Fu, M. Hagerott and A.V. Nurmikko, Molecular beam epitaxy of pseudomorphic ZnTe/AlSb/GaSb 228 (1990) 344

P. Basmaji, A.M. Ceschin, M. Siu Li, O. Hipólito, A.A. Bernussi, F. Iikawa and P. Motisuke, MBE growth and characterization of δ-doping in GaAs and GaAs/Si 228 (1990) 356

Photoconductivity

M. Nithisoontorn, K. Unterrainer, S. Michaelis, N. Sawaki, E. Gornik and H. Kano, First observation of the forbidden 1S excitons in GaAs/AlGaAs multiple quantum wells via two-photon absorption spectra 228 (1990) 53

H.T. Grahn, H. Schneider and K. von Klitzing, Spatial distribution of high-field domains in GaAs–AlAs superlattices 228 (1990) 84

F. Laruelle, B. Etienne, J. Barrau, K. Khirouni, J.C. Brabant, T. Amand and M. Brousseau, Wavefunction localization in Fibonacci quasiperiodic GaAs/GaAlAs superlattices under electric field 228 (1990) 92

R.J. Warburton, G.M. Sundaram, R.J. Nicholas, S.K. Haywood, G.J. Rees, N.J. Mason and P.J. Walker, Strain reconstruction of the valence band in $Ga_{1-x}In_xSb/GaSb$ quantum wells 228 (1990) 270

X.M. Fang, X.C. Shen, H.Q. Hou, W. Feng, J.M. Zhou and F. Koch, Photocurrent spectroscopy of strained-layer InGaAs–GaAs multiple quantum wells 228 (1990) 351

H. Schneider, H.T. Grahn and K. von Klitzing, Tunneling resonances and miniband conduction in superlattices 228 (1990) 362

G. Berthold, J. Smoliner, G. Strasser, E. Gornik and G. Weimann, Subbands and photoconductivity in two barrier-separated 2D electron gas systems 228 (1990) 399

H. Le Person, J.F. Palmier, C. Minot, J.C. Esnault and F. Mollot, Time of flight of electrons and holes at 77 and 300 K in GaAs/AlAs superlattices 228 (1990) 441

R. Heinrich, R. Zachai, M. Besson, T. Egeler, G. Abstreiter, W. Schlapp and G. Weimann, Negative infrared photoconductivity in narrow GaAs/AlGaAs multiple quantum well structures 228 (1990) 465

Photoelectron spectroscopy

S.G. Konnikov and K.Ju. Pogrebitsky, New nondestructive composition depth profiling method for diagnostics of multilayer quantum-well structures 228 (1990) 532

Raman scattering

S.M. Durbin, M. Kobayashi, Q. Fu, N. Pelekanos, R.L. Gunshor and A.V. Nurmikko, ZnTe/MnTe: a new metastable wide gap II–VI heterostructure 228 (1990) 33

J. Menéndez, A. Pinczuk, J.P. Valladares, L.N. Pfeiffer, K.W. West, A.C. Gossard and J.H. English, Raman investigation of strong quasi-direct optical transitions in ultrathin GaAs–AlAs superlattices 228 (1990) 65

R. Merlin, N. Mestres, A. McKiernan, J.E. Oh and P.K. Bhattacharya, Charge-density domains in photoexcited quantum-well structures 228 (1990) 88

M.C. Tatham, J.F. Ryan and C.T. Foxon, Time-resolved Raman scattering measurement of electron–optical phonon intersubband relaxation in GaAs quantum wells 228 (1990) 127

M. Nakayama, M. Ishida and N. Sano, Interface-phonon polaritons in GaAs/AlAs heterostructures 228 (1990) 131

T.A. Gant, D.J. Lockwood, J.-M. Baribeau and A.H. MacDonald, Raman scattering studies of phonons in quasiperiodic superlattices based on generalizations of the Fibonacci sequence 228 (1990) 135

M. Recio, G. Armelles, A. Ruiz, A. Mazuelas and F. Briones, Strain distribution and structural characterization of short period GaAs–GaP strained superlattices by Raman and X-ray scattering 228 (1990) 139

D. Gammon, B.V. Shanabrook and W. Tseng, A Raman scattering and far-infrared magneto-absorption study of donors in a quasi-two-dimensional electron gas 228 (1990) 147

B. Jusserand, F. Mollot and D. Paquet, Forward scattering on short period GaAs/AlAs superlattices 228 (1990) 151

F. Calle, J.M. Calleja, C. Tejedor, F. Briones, J.L. de Miguel and K. Ploog, Resonant Raman scattering in GaAs–AlAs coupled double wells 228 (1990) 176

I. Brener, E. Cohen, A. Ron and L.N. Pfeiffer, Resonant Raman scattering by acceptors and LO phonons in GaAs/AlGaAs multiple quantum wells 228 (1990) 180

C. López, F. Meseguer, J. Sánchez-Dehesa and K. Ploog, Magnetoluminescence studies of modulation n-doped GaAs–AlGaAs multiple quantum wells 228 (1990) 202

G. Scamarcio, A. Cingolani, R. Cingolani and K. Ploog, Optical and vibrational properties of $Al_xGa_{1-x}As/AlAs$ multiple quantum wells near the direct indirect cross-over 228 (1990) 213

A.C. Maciel, M.C. Tatham, J.F. Ryan, J.M. Worlock, R.E. Nahory, J.P. Harbison and L.T. Florez, Raman scattering from electronic excitations in periodically δ-doped GaAs 228 (1990) 251
C.M. Sotomayor Torres, M. Watt, H.E.G. Arnot, R. Glew, R. Cusco Cornet, T.M. Kerr, S. Thoms and S.P. Beaumont, Optical spectroscopy of GaAs-based nanostructures 228 (1990) 275

Reflection spectroscopy

P. Voisin, Wannier quantization and novel electro-optical properties in semiconductor superlattices 228 (1990) 74
D.D. Smith, M. Dutta, X.C. Liu, A.F. Terzis, A. Petrou, M.W. Cole and P.G. Newman, GaAs–AlAs quantum well magneto-exciton spectrum – theory and experiment 228 (1990) 184
B. Rockwell, H.R. Chandrasekhar, M. Chandrasekhar, F.H. Pollak, H. Shen, L.L. Chang, W.I. Wang and L. Esaki, Spectroscopic studies of strained-layer GaSb–AlSb superlattices 228 (1990) 322
A. Ksendzov, H. Shen, F.H. Pollak and D.P. Bour, Photoreflectance study of $In_xGa_{1-x}As/GaAs$ single quantum wells 228 (1990) 326
P. Basmaji, A.M. Ceschin, M. Siu Li, O. Hipólito, A.A. Bernussi, F. Iikawa and P. Motisuke, MBE growth and characterization of δ-doping in GaAs and GaAs/Si 228 (1990) 356

Semiconductors

T. Mimura, HEMT technology: impact on computer and communication systems 228 (1990) 504

Silicides

J. Henz, J. Hugi, M. Ospelt and H. von Känel, Fabrication and electrical properties of ultrathin $CoSi_2$/Si heterostructures 228 (1990) 9

Silicon

T.A. Gant, D.J. Lockwood, J.-M. Baribeau and A.H. MacDonald, Raman scattering studies of phonons in quasiperiodic superlattices based on generalizations of the Fibonacci sequence 228 (1990) 135
G. Tempel, F. Müller, N. Schwarz, F. Koch, G. Weimann, H.P. Zeindl and I. Eisele, Infrared excitation of the subbands of a δ-layer in GaAs and Si 228 (1990) 247
M. Santos, T. Sajoto, A.-M. Lanzillotto, A. Zrenner and M. Shayegan, Migration of Si in δ-doped GaAs and $Al_xGa_{1-x}As$: effect of substrate temperature 228 (1990) 255
R. Zachai, K. Eberl, G. Abstreiter, E. Kasper and H. Kibbel, Photoluminescence in short period Si/Ge strained layer superlattices grown on Si and Ge substrates 228 (1990) 267
Xun Wang, K.M. Chen, G.L. Jin, C. Sheng, G.L. Zhou, W.D. Jiang, X.J. Zhang and M.R. Yu, RHEED intensity oscillations of MBE grown Ge/Si ultra-thin multi-layered structures 228 (1990) 334
P. Basmaji, A.M. Ceschin, M. Siu Li, O. Hipólito, A.A. Bernussi, F. Iikawa and P. Motisuke, MBE growth and characterization of δ-doping in GaAs and GaAs/Si 228 (1990) 356
J. Alsmeier, E. Batke and J.P. Kotthaus, The transition to quasi one- or zero-dimensionality in laterally periodic MOS devices on silicon 228 (1990) 524
P.M. Koenraad, A.P.J. Voncken, J. Singleton, F.A.P. Blom, C.J.G.M. Langerak, M.R. Leys, J.A.A.J. Perenboom, S.J.R.M. Spermon, W.C. van Vleuten and J.H. Wolter, Characterization of silicon δ-doped GaAs grown by MBE at various temperatures 228 (1990) 538

Superlattices

T. Fukui, H. Saito, Y. Tokura, K. Tsubaki and N. Susa, $(AlAs)_{1/2}(GaAs)_{1/2}$ fractional-layer superlattices grown on (001) vicinal GaAs substrates by MOCVD 228 (1990) 20
P.M. Petroff, M. Tsuchiya and L.A. Coldren, Self-organizing epitaxial growth for the deposition of novel superlattices 228 (1990) 24
M. Voos, J. Manasses, J.M. Berroir, Y. Guldner, J.P. Vieren, X. Chu and J.P. Faurie, Electron cyclotron resonance in type III HgZnTe–CdTe superlattices 228 (1990) 37
M.P. Halsall, J.E. Nicholls, J.J. Davies, P.J. Wright and B. Cockayne, Photoluminescence studies of CdS/CdSe

wurtzite superlattices; evidence for large piezoelectric effects 228 (1990) 41
C.A. Hoffman, J.R. Meyer, F.J. Bartoli, Y. Lansari, J.W. Cook, Jr. and J.F. Schetzina, Transport investigation of HgTe–CdTe single and multiple quantum wells 228 (1990) 45
S.Y. Ren, J. Shen, Run-Di Hong, S. Klemm, M.-H. Tsai and J.D. Dow, Deep levels and shallow–deep transitions in $ZnSe/Zn_{1-x}Mn_xSe$ superlattices 228 (1990) 49
N.J. Pulsford, R.J. Nicholas, P. Dawson, K.J. Moore, G. Duggan and C.T. Foxon, Γ- and X-miniband structure in GaAs–AlAs short period superlattices 228 (1990) 62
J. Menéndez, A. Pinczuk, J.P. Valladares, L.N. Pfeiffer, K.W. West, A.C. Gossard and J.H. English, Raman investigation of strong quasi-direct optical transitions in ultrathin GaAs–AlAs superlattices 228 (1990) 65
H. Wang, J.T. Remillard, M.D. Webb, D.G. Steel, J. Pamulapati, J.E. Oh and P.K. Bhattacharya, High resolution laser spectroscopy of relaxation and the excitation lineshape of excitons in GaAs quantum well structures 228 (1990) 69
P. Voisin, Wannier quantization and novel electro-optical properties in semiconductor superlattices 228 (1990) 74
F. Agulló-Rueda, E.E. Mendez, J.A. Brum and J.M. Hong, Coherence and localization in superlattices under electric fields 228 (1990) 80
H.T. Grahn, H. Schneider and K. von Klitzing, Spatial distribution of high-field domains in GaAs–AlAs superlattices 228 (1990) 84
R. Merlin, N. Mestres, A. McKiernan, J.E. Oh and P.K. Bhattacharya, Charge-density domains in photoexcited quantum-well structures 228 (1990) 88
F. Laruelle, B. Etienne, J. Barrau, K. Khirouni, J.C. Brabant, T. Amand and M. Brousseau, Wavefunction localization in Fibonacci quasiperiodic GaAs/GaAlAs superlattices under electric field 228 (1990) 92
A. Fasolino and E. Molinari, Calculations of phonon spectra in III–V and Si–Ge superlattices: a tool for structural characterization 228 (1990) 112
M. Helm, P. England, E. Colas, F. DeRosa and S.J. Allen, Jr., Intersubband emission from quantum wells and superlattices 228 (1990) 120
M. Olszakier, E. Ehrenfreund, E. Cohen, J. Bajaj and G.J. Sullivan, Intersubband absorption by photoinduced excitons in undoped multi-quantum-wells 228 (1990) 123
M.C. Tatham, J.F. Ryan and C.T. Foxon, Time-resolved Raman scattering measurement of electron–optical phonon intersubband relaxation in GaAs quantum wells 228 (1990) 127
T.A. Gant, D.J. Lockwood, J.-M. Baribeau and A.H. MacDonald, Raman scattering studies of phonons in quasiperiodic superlattices based on generalizations of the Fibonacci sequence 228 (1990) 135
M. Recio, G. Armelles, A. Ruiz, A. Mazuelas and F. Briones, Strain distribution and structural characterization of short period GaAs–GaP strained superlattices by Raman and X-ray scattering 228 (1990) 139
P. Hawrylak and M. Grabowski, Nonlinear optical transmission through a multiple quantum well system 228 (1990) 144
D. Gammon, B.V. Shanabrook and W. Tseng, A Raman scattering and far-infrared magneto-absorption study of donors in a quasi-two-dimensional electron gas 228 (1990) 147
B. Jusserand, F. Mollot and D. Paquet, Forward scattering on short period GaAs/AlAs superlattices 228 (1990) 151
H. Tsuchiya, Y. Shakuda and H. Kata, Intersubband absorption changes in GaAs/AlGaAs MQW induced by external light 228 (1990) 172
F. Calle, J.M. Calleja, C. Tejedor, F. Briones, J.L. de Miguel and K. Ploog, Resonant Raman scattering in GaAs–AlAs coupled double wells 228 (1990) 176
I. Brener, E. Cohen, A. Ron and L.N. Pfeiffer, Resonant Raman scattering by acceptors and LO phonons in GaAs/AlGaAs multiple quantum wells 228 (1990) 180
N.F. Johnson and H. Ehrenreich, Infrared optical properties of III–V and II–VI superlattices 228 (1990) 197
H. Fujimoto, C. Hamaguchi, T. Nakazawa, K. Imanishi, K. Taniguchi and S. Sasa, Direct and indirect transitions in $(GaAs)_m/(AlAs)_5$ superlattices 228 (1990) 206
B. Lambert, B. Sermage, B. Deveaud, F. Clerot, A. Chomette and A. Regreny, Radiative and non-radiative recombination in GaAs–AlGaAs superlattices 228 (1990) 210
R. Cingolani, M. Holtz, R. Muralidharan, K. Ploog, K. Reimann and K. Syas-

sen, Type I–type II transition in ultra short period GaAs/AlAs superlattices revealed by luminescence under high-excitation intensity and high pressure 228 (1990) 217

D.D. Awschalom, J.M. Hong and L.L. Chang, Magnetic observations of carrier quantization and dimensional crossover in diluted magnetic semiconductor superlattices 228 (1990) 220

M.R. Freeman, D.D. Awschalom, J.M. Hong and L.L. Chang, Ultrafast polarization spectroscopy of diluted magnetic semiconductor superlattices 228 (1990) 233

H. Clemens, H. Krenn, P.C. Weilguni, U. Stromberger, G. Bauer and H. Pascher, Growth and characterization of dilute magnetic $PbTe/Pb_{1-x}Mn_xTe$ superlattices 228 (1990) 236

E.F. Schubert, Optical properties of δ-doped doping superlattices 228 (1990) 240

M. Santos, T. Sajoto, A.-M. Lanzillotto, A. Zrenner and M. Shayegan, Migration of Si in δ-doped GaAs and $Al_xGa_{1-x}As$: effect of substrate temperature 228 (1990) 255

J.Y. Tsao and B.W. Dodson, Time, temperature and excess stress: relaxation in strained heterostructures 228 (1990) 260

R. Zachai, K. Eberl, G. Abstreiter, E. Kasper and H. Kibbel, Photoluminescence in short period Si/Ge strained layer superlattices grown on Si and Ge substrates 228 (1990) 267

Y. Tokura, K. Tsubaki and N. Susa, Electronic states in an AlGaAs–GaAs modulation-doped hetero-interface with a 10 nm-order periodic structure 228 (1990) 280

G. Duggan, K.J. Moore, K. Woodbridge and C. Roberts, (InGa)As–GaAs strained layer quantum wells – excitonic properties and electronic structure 228 (1990) 310

E.S. Koteles, D.A. Owens, D.C. Bertolet, Jung-Kuei Hsu and Kei May Lau, Reversal of light- and heavy-hole valence bands in strained GaAsP/AlGaAs quantum wells 228 (1990) 314

B. Rockwell, H.R. Chandrasekhar, M. Chandrasekhar, F.H. Pollak, H. Shen, L.L. Chang, W.I. Wang and L. Esaki, Spectroscopic studies of strained-layer GaSb–AlSb superlattices 228 (1990) 322

A. Ksendzov, H. Shen, F.H. Pollak and D.P. Bour, Photoreflectance study of $In_xGa_{1-x}As/GaAs$ single quantum wells 228 (1990) 326

H. Nickel, R. Lösch, W. Schlapp, H. Leier and A. Forchel, $In_xGa_{1-x}As/GaAs$ pseudomorphic quantum wells – growth and thermal stability 228 (1990) 340

D. Morris, C. Lacelle, A.P. Roth, P. Maigne and J.L. Brebner, Optical and structural characterization of InGaAs/GaAs superlattices with increasing number of periods 228 (1990) 347

X.M. Fang, X.C. Shen, H.Q. Hou, W. Feng, J.M. Zhou and F. Koch, Photocurrent spectroscopy of strained-layer InGaAs–GaAs multiple quantum wells 228 (1990) 351

T.J. Gregory, J.E. Nicholls, J.J. Davies, C.P. Hilton, W.E. Hagston, B. Lunn and D.E. Ashenford, Band offset determination in $CdTe/Cd_{1-x}Mn_xTe$ MQWs grown on InSb substrates 228 (1990) 359

H. Schneider, H.T. Grahn and K. von Klitzing, Tunneling resonances and miniband conduction in superlattices 228 (1990) 362

D.G. Hayes, M.S. Skolnick, P.E. Simmonds, L. Eaves, D.P. Halliday, M.L. Leadbeater, M. Henini, O.H. Hughes, G. Hill and M.A. Pate, Optical investigation of charge accumulation and bistability in an asymmetric double barrier resonant tunneling heterostructure 228 (1990) 373

H.W. Liu, R. Ferreira, G. Bastard, C. Delalande, J.F. Palmier and B. Etienne, Optical study of assisted tunneling in biased double quantum well structures 228 (1990) 383

T.B. Norris, G.A. Mourou, X.J. Song, L.F. Eastman, N. Vodjdani, B. Vinter and C. Weisbuch, Time-resolved photoluminescence spectroscopy of GaAs quantum well tunneling structures 228 (1990) 393

Yuanlin Xie, Wenqin Cheng, Yi Huang, Zhenghao Chen, Zhidong Lu, Guozhen Yang, Shijie Gu and Junming Zhou, Study on optical properties of planar modulation structures of AlGaAs/GaAs superlattices and quantum wells 228 (1990) 403

M. Tanaka, J. Motohisa and H. Sakaki, Formation of in-plane superlattice and quantum wire states in grid inserted heterostructures with period of 80–160 Å: anisotropy of electronic states 228 (1990) 408

K. Kash, J.M. Worlock, D.D. Mahoney, A.S. Gozdz, B.P. van der Gaag, J.P. Harbison, P.S.D. Lin and L.T. Florez, Optical properties of quantum wires produced by strain patterning of GaAs–AlGaAs quantum wells 228 (1990) 415

J. Zhang, Y.S. Joe and S.E. Ulloa, Surface resonances, tunneling and optical response of doped superlattices 228 (1990) 422

I. Mehdi, R.K. Mains, G.I. Haddad and U.K. Reddy, Properties and device applications of deep quantum well resonant tunneling structures 228 (1990) 426
H. Le Person, J.F. Palmier, C. Minot, J.C. Esnault and F. Mollot, Time of flight of electrons and holes at 77 and 300 K in GaAs/AlAs superlattices 228 (1990) 441
B. Lambert, B. Deveaud, A. Chomette, F. Clerot, A. Regreny and B. Sermage, Temperature dependence of electronic vertical transport in short period GaAs–AlGaAs superlattices 228 (1990) 446
R. Heinrich, R. Zachai, M. Besson, T. Egeler, G. Abstreiter, W. Schlapp and G. Weimann, Negative infrared photoconductivity in narrow GaAs/AlGaAs multiple quantum well structures 228 (1990) 465
J.-B. Xia, Pseudopotential approach to long-period semiconductor superlattices 228 (1990) 476
K.J. Duff and K.C. Hass, Multi-band envelope function calculations for sawtooth superlattices 228 (1990) 479
A. Wixforth, M. Sundaram, D. Donnelly, J.H. English and A.C. Gossard, Graded potential wells with quasi-uniform charge distribution 228 (1990) 489
H. Lin, K.H. Gulden, P. Hilbig, P. Kiesel, P. Riel and G.H. Döhler, Anomalous in-plane drift and diffusion of non-equilibrium charge carriers in n–i–p–i doping superlattices 228 (1990) 500
P.S. Kop'ev, SCH lasers using short period superlattices 228 (1990) 514
R.A. Puechner, Jun Ma, R. Mezenner, W.-P. Liu, A.M. Kriman, G.N. Maracas, G. Bernstein, D.K. Ferry, P. Chu, H.H. Wieder and P.G. Newman, Magnetoconductance in lateral surface superlattices 228 (1990) 520
J. Alsmeier, E. Batke and J.P. Kotthaus, The transition to quasi one- or zero-dimensionality in laterally periodic MOS devices on silicon 228 (1990) 524
C.T. Liu, K. Nakamura, D.C. Tsui, K. Ismail, D.A. Antoniadis and H.I. Smith, Far-infrared transmission measurements on grid-gate GaAs/AlGaAs lateral-surface-superlattice structures 228 (1990) 527
S.G. Konnikov and K.Ju. Pogrebitsky, New nondestructive composition depth profiling method for diagnostics of multilayer quantum-well structures 228 (1990) 532

Surface phonons and adsorbate vibrations

A. Fasolino and E. Molinari, Calculations of phonon spectra in III–V and Si–Ge superlattices: a tool for structural characterization 228 (1990) 112
M. Nakayama, M. Ishida and N. Sano, Interface-phonon polaritons in GaAs/AlAs heterostructures 228 (1990) 131
I. Brener, E. Cohen, A. Ron and L.N. Pfeiffer, Resonant Raman scattering by acceptors and LO phonons in GaAs/AlGaAs multiple quantum wells 228 (1990) 180
C.M. Sotomayor Torres, M. Watt, H.E.G. Arnot, R. Glew, R. Cusco Cornet, T.M. Kerr, S. Thoms and S.P. Beaumont, Optical spectroscopy of GaAs-based nanostructures 228 (1990) 275

Surface stress

J.Y. Tsao and B.W. Dodson, Time, temperature and excess stress: relaxation in strained heterostructures 228 (1990) 260

Tunneling

G. Platero, P.A. Schulz, L. Brey and C. Tejedor, Quantum transmission channels for magnetotunneling in semiconductor microstructures 228 (1990) 291
S. Muto, A. Tackeuchi, T. Inata, E. Miyauchi and T. Fujii, Picosecond characterization of InGaAs/InAlAs resonant tunneling barriers grown by MBE 228 (1990) 370
D.G. Hayes, M.S. Skolnick, P.E. Simmonds, L. Eaves, D.P. Halliday, M.L. Leadbeater, M. Henini, O.H. Hughes, G. Hill and M.A. Pate, Optical investigation of charge accumulation and bistability in an asymmetric double barrier resonant tunneling heterostructure 228 (1990) 373
S. Ben Amor, K.P. Martin, J.J.L. Rascol, R.J. Higgins, R.C. Potter, A.A. Lakhani and H. Hier, Magneto-electric states in wide-well double barrier tunneling structures 228 (1990) 378
H.W. Liu, R. Ferreira, G. Bastard, C. Delalande, J.F. Palmier and B. Etienne, Optical study of assisted tunneling in biased double quantum well structures 228 (1990) 383

C.G. Smith, M. Pepper, H. Ahmed, J.E.F. Frost, D.G. Hasko, R. Newbury, D.C. Peacock, D.A. Ritchie and G.A.C. Jones, One dimensional electron tunneling and related phenomena 228 (1990) 387

T.B. Norris, G.A. Mourou, X.J. Song, L.F. Eastman, N. Vodjdani, B. Vinter and C. Weisbuch, Time-resolved photoluminescence spectroscopy of GaAs quantum well tunneling structures 228 (1990) 393

G. Berthold, J. Smoliner, G. Strasser, E. Gornik and G. Weimann, Subbands and photoconductivity in two barrier-separated 2D electron gas systems 228 (1990) 399

R. Tsu and F. Zypman, New insights in the physics of resonant tunneling 228 (1990) 418

J. Zhang, Y.S. Joe and S.E. Ulloa, Surface resonances, tunneling and optical response of doped superlattices 228 (1990) 422

I. Mehdi, R.K. Mains, G.I. Haddad and U.K. Reddy, Properties and device applications of deep quantum well resonant tunneling structures 228 (1990) 426

M. Henini, M.L. Leadbeater, E.S. Alves, L. Eaves, O.H. Hughes, G. Hill and M.A. Pate, The effect of conduction band anisotropy on hybrid magneto-electric states in resonant tunneling devices 228 (1990) 433

T.M. Fromhold, F.W. Sheard and G.A. Toombs, Effect of a transverse magnetic field on tunneling in single- and double-barrier structures 228 (1990) 437

H. Kurata, M. Tsuchiya and H. Sakaki, A novel optical bistability device consisting of resonant tunneling diode and quantum Stark modulator: experimental demonstration 228 (1990) 468

F. Claro, F. Vivanco and M. Pacheco, Resonant tunneling: relation between the transmission coefficient and a measurable quantity 228 (1990) 486

X-ray diffraction

A. Krol, C.J. Sher, D.R. Storch, S.C. Woronick, Y.H. Kao, L.L. Chang and H. Munekata, Soft X-ray investigation of the effect of growth conditions on InAs/GaAs heterostructures 228 (1990) 108

H. Clemens, H. Krenn, P.C. Weilguni, U. Stromberger, G. Bauer and H. Pascher, Growth and characterization of dilute magnetic $PbTe/Pb_{1-x}Mn_xTe$ superlattices 228 (1990) 236